Peak gate current (t_p=20 s , T_j=150)	I_{GM}	4	A
Average gate power dissipation (T_j=150)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	25	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	40	mA
				60	
I_H	I_T =500mA		MAX.	30	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	5000	V s
	V_D=540V Gate Open T_j =150			2000	
(dI/dt)c	(dV/dt)c=1 9 V j=1 0		MIN.	15	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	2	s
t_{off}				30	
V_{CL}	I_{CL}=0.1mA t_p=1ms		MIN.	850	V

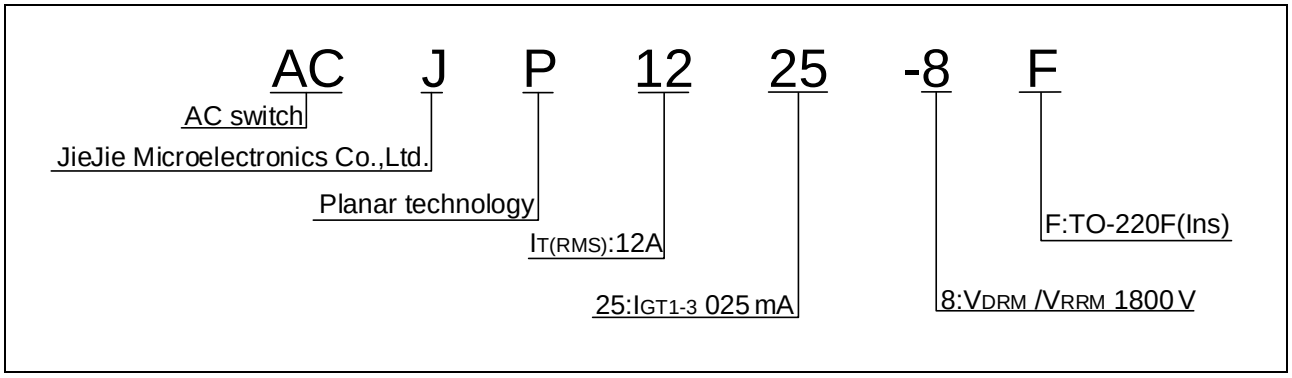
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX .)	Unit
V_{TM}	I_{TM} =17A t_p=380 s	T_j=25	1.55	V
V_{TO}	Threshold voltage	T_j=150	0.73	V
R_D	Dynamic resistance	T_j=150	40	P
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	3	A
I_{RRM}		T_j=150	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.8	/W
$R_{th(j-a)}$	junction to ambient (AC)	50	/W

ORDERING INFORMATION



MARKING

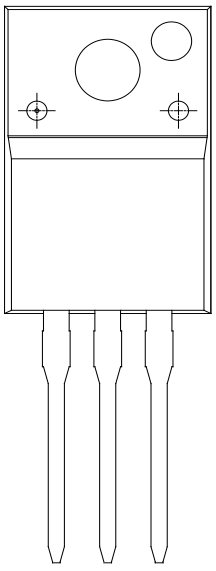


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJP1225-8F	800	25	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2026	A.1.0	Last updated

PACKAGE MECHANICAL DATA ADEBCC2C3V1C2C3C2V1C2V1



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